

<b>Crystal Properties</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Crystalline structure	-	Monocrystalline	
Growth technique	-	Czochralski (Cz) or MCz	
Orientation	-	<100> ±1°	
Slice orientation	Degrees	ON ±1.0°	
<b>Electrical Properties</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Conductance type	-	P-type	
Dopant	-	Boron	
Resistivity	Ω-cm	1 - 30	
<b>Geometrical Properties</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Diameter	mm	300±0.20	
Thickness	μm	775±25	
TTV	μm	≤3	
Warp	μm	≤25	
Bow	μm	≤25	
Notch	-	SEMI Standard	
Notch depth	mm	1.0 + 0.25 – 0.00	
Notch angle	-	90° +5° -1°	
Notch orientation	-	<110>±2°	
<b>Surface Appearance</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Front surface	-	Polished	
Back surface	-	Polished	
Frontside particles ≥0.065 μm (LPD/COP)	No./wafer	≤50	
Edge exclusion	mm	3.0	
<b>Wafer Identification</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Lasermark	-	SEMI Standard Backside T7 and M12	
<b>Surface Metals</b>			
<b>APPLICABLE METALS</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Al, Ca, Cl, Cr, Cu, Fe, K, Na, Ni, Zn	Atoms/cm <sup>2</sup>	≤1E10	